

# Small-Signal Model Parameters

- *Diode Resistance* ( $r_D$ )/*Diode Conductance* ( $g_D$ ):

$$r_D = (g_D)^{-1} = \left( \frac{\partial I_D}{\partial V_D} \right)^{-1} \bigg|_{I_D = I_{DQ}} = \frac{V_T}{I_{DQ}}$$

- For  $I_{DQ} = 1 \text{ mA}$ ,  $r_D = 26 \Omega$
- *Under forward bias*, diode offers *very small resistance*

- **Diode Capacitance** ( $C_D$ ):

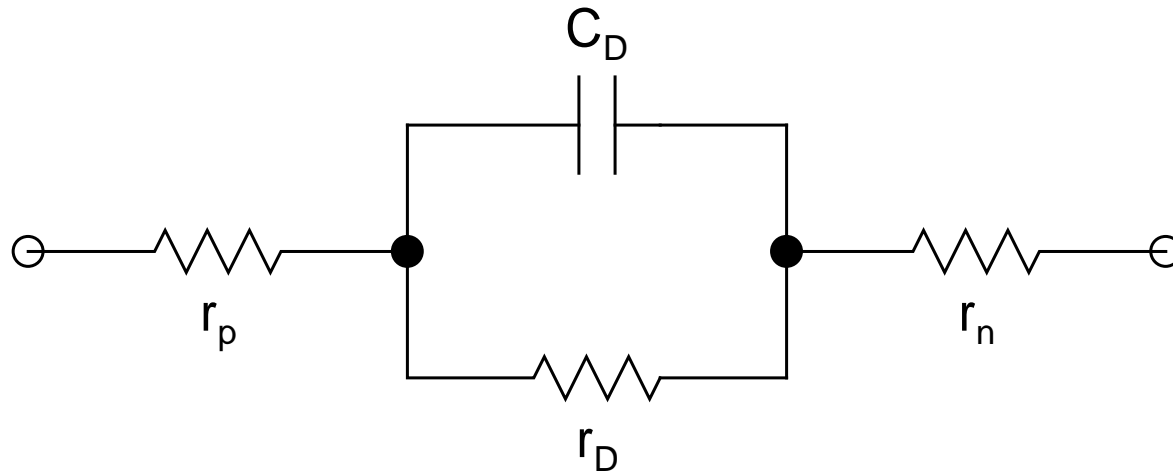
- $C_D = C_{\text{dep}} + C_{\text{diff}}$   
 $= C_{\text{dep0}}/(1 - V_D/V_0)^m + \tau/r_D$

- m: *Grading coefficient*

- (1/2 for *abrupt step junction*, 1/3 for *linearly graded junction*)

- *Both  $r_D$  and  $C_D$  appear in parallel across the junction*
- *The two quasi-neutral resistance  $r_p$  and  $r_n$  appear in series with this combination*

# Small-Signal Equivalent



- *In absence of  $r_p$  and  $r_n$ , it's just a parallel RC circuit, and shorts out at high frequency*
  - *Diode time constant  $\tau_D = r_D C_D = \tau$*